

Features

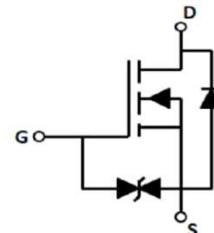
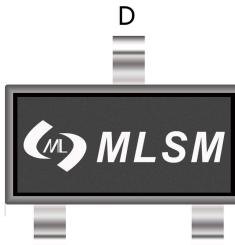
- Reliable and Rugged
- Fast Switching Speed
- ESD protected

Product Summary

V _{DS}	R _{DS(ON)} MAX	I _D MAX
30V	400mΩ@10V	0.75A
	600mΩ@4.5V	

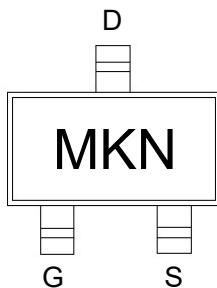
Application

- Battery Operated Systems
- Portable Equipment



SOT-523 top view

Schematic diagram



MKN: Device code



Halogen-Free

Marking and pin assignment

Absolute Maximum Ratings (TA=25°C unless otherwise noted)

Symbol	Parameter	Rating	Unit
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Common Ratings (TC=25°C Unless Otherwise Noted)

V _{DS}	Drain-Source Breakdown Voltage	30	V	
V _{GS}	Gate-Source Voltage	±12	V	
T _J	Maximum Junction Temperature	150	°C	
T _{STG}	Storage Temperature Range	-50 to 155	°C	
I _S	Diode Continuous Forward Current	Tc=25°C	0.75	A

Mounted on Large Heat Sink

I _{DM}	Pulse Drain Current Tested	Tc=25°C	1.8	A
I _D	Continuous Drain Current	Tc=25°C	0.75	A
P _D	Maximum Power Dissipation	Tc=25°C	0.35	W
R _{θJA}	Thermal Resistance Junction-Ambient		350	°C/W

Ordering Information (Example)

Type	Package	Marking	Minimum Package(pcs)	Inner Box Quantity(pcs)	Outer Carton Quantity(pcs)	Delivery Mode
MLS1302KT	SOT-523	MKN	3,000	45,000	180,000	7" reel

Electrical Characteristics (TJ=25°C unless otherwise noted)						
Symbol	Parameter	Condition	Min	Typ	Max	Unit
Static Electrical Characteristics @ TJ = 25°C (unless otherwise stated)						
BV _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250μA	30	--	--	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =30V, V _{GS} =0V	--	--	1	μA
I _{GSS}	Gate-Body Leakage Current	V _{GS} =±12V, V _{DS} =0V	--	--	±20	μA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250μA	0.35	0.7	1.1	V
R _{DS(on)}	Drain-Source On-State Resistance	V _{GS} =10V, I _D =0.5A	--	330	400	mΩ
		V _{GS} =4.5V, I _D =0.3A	--	360	600	mΩ
		V _{GS} =2.5V, I _D =0.1A	--	--	800	mΩ
Dynamic Electrical Characteristics @ TJ = 25°C (unless otherwise stated)						
C _{ISS}	Input Capacitance	V _{DS} =15V, V _{GS} =0V, f=1MHz	--	38	--	pF
C _{OSS}	Output Capacitance		--	5.1	--	pF
C _{RSS}	Reverse Transfer Capacitance		--	3.2	--	pF
Switching Characteristics						
Q _g	Total Gate Charge	V _{DS} =15V, I _D =0.75A, V _{GS} =4.5V	--	0.8	--	nC
Q _{gs}	Gate Source Charge		--	0.3	--	nC
Q _{gd}	Gate Drain Charge		--	0.17	--	nC
t _{d(on)}	Turn-on Delay Time	V _{DD} =15V, I _D =0.75A, V _{GS} =4.5V, R _G =6Ω	--	5.5	--	nS
t _r	Turn-on Rise Time		--	20.3	--	nS
t _{d(off)}	Turn-Off Delay Time		--	34.5	--	nS
t _f	Turn-Off Fall Time		--	30	--	nS
Source- Drain Diode Characteristics						
V _{SD}	Forward on voltage	T _j =25°C, I _S =0.75A	--	--	1.2	V

Typical Operating Characteristics

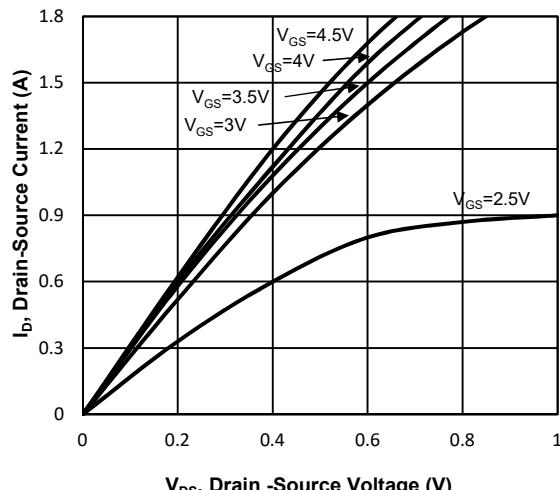


Fig1. Typical Output Characteristics

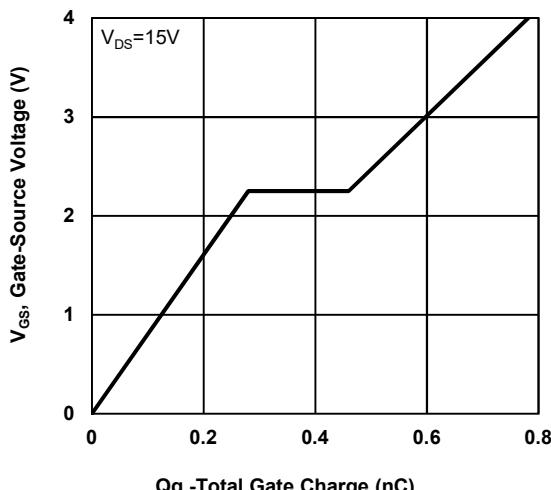


Fig2. Typical Gate Charge Vs.Gate-Source Voltage

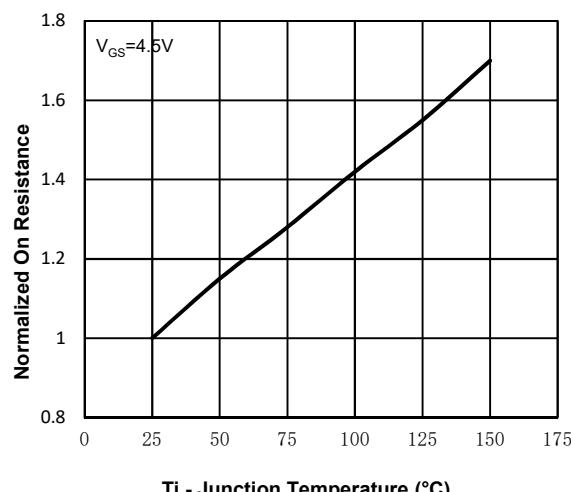


Fig3. Normalized On-Resistance Vs. Temperature

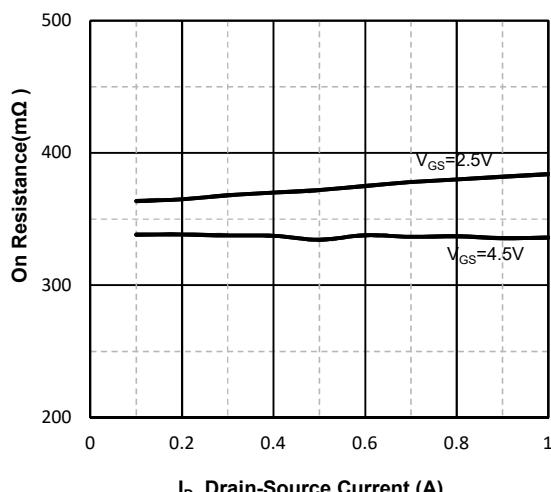


Fig4. On-Resistance Vs. Drain-Source Current

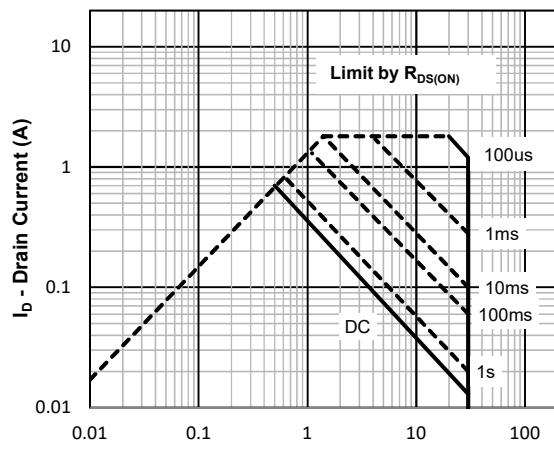


Fig5. Maximum Safe Operating Area

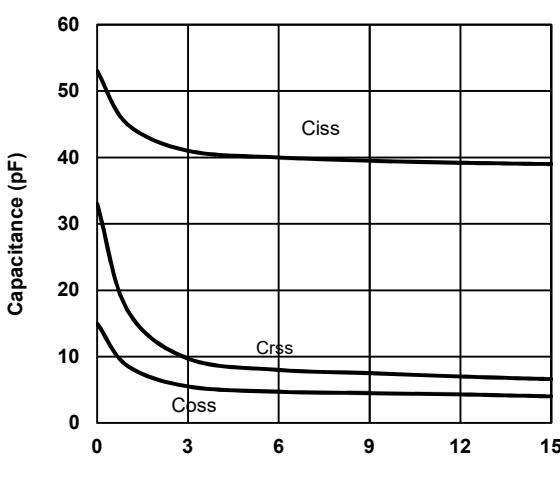
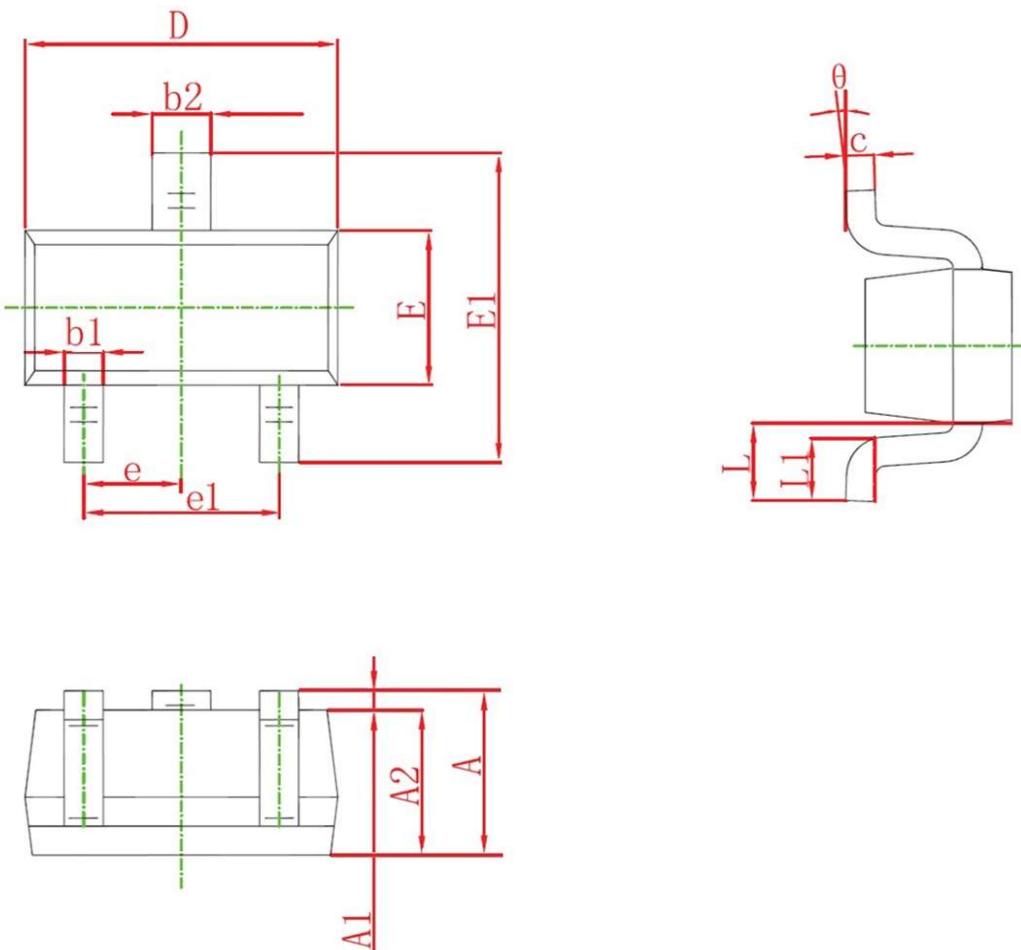


Fig6 Typical Capacitance Vs.Drain-Source Voltage

SOT-523 Package information



Symbol	Dimensions in Millimeters(mm)		Dimensions In Inches	
	Min	Max	Min	Max
A	0.700	0.900	0.028	0.035
A1	0.000	0.100	0.000	0.004
A2	0.700	0.800	0.028	0.031
b1	0.150	0.250	0.006	0.010
b2	0.250	0.350	0.010	0.014
c	0.100	0.200	0.004	0.008
D	1.500	1.700	0.059	0.067
E	0.700	0.900	0.028	0.035
E1	1.450	1.750	0.057	0.069
e	0.500TYP		0.020TYP	
e1	0.900	1.100	0.035	0.043
L	0.400REF		0.016REF	
L1	0.260	0.460	0.010	0.018
θ	0°	8°	0°	8°